

**INFORMATION DISCLOSURE  
CITATION FORM FOR  
PATENT APPLICATION  
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Applicant(s): Hyungjun KIM et al.

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**U.S. PATENTS**

Initials	Patent Number	Issue Date	Name	Class	Sub-class	Filing date

**FOREIGN PATENT DOCUMENTS**

Initials	Document Number	Date	Country	Name	Translation? Yes/No/n/a

**OTHER DOCUMENTS (Title, Author, Date, Pages, Etc., if known)**

	Kim et al., Diffusion barrier properties of transition metal thin films grown by plasma-enhanced atomic layer deposition, J. Vac. Sci. Technol. B 20(4), J/A 2002
	Kim et al., Growth kinetics and initial stage growth during plasma-enhanced Ti atomic layer deposition, J. Vac. Sci. Technol. A 20(3), May/June 2002
	Rossnagel et al., Plasma-enhanced atomic layer deposition of Ta and Ti for interconnect diffusion barriers, J. Vac. Sci. Technol. B 18(4), July/Aug 2002

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